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	Application No.	Applicant(s)	Ø
	10/776,939	JOHNSON, MARK B.	
Notice of Allowability	Examiner	Art Unit	
	Gene N Auduong	2818	
Th MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGOR Of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED in or other appropriate commu GHTS. This application is so and MPEP 1308.	this application. If not included nication will be mailed in due co	ourse. THIS
1. $igspace$ This communication is responsive to <u>application filed 2-10-</u> 0	<u>04</u> .		
2. X The allowed claim(s) is/are <u>1-39</u> .			
3. $igotimes$ The drawings filed on $ extit{10 February 2004}$ are accepted by th	e Examiner.		
4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give for a complete such as the proper No./Mail Date (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the complete sheet. Replacement sheet(s) should be Required by the depose attached Examiner's comment regarding REQUIREMENT is	been received. been received in Application cuments have been received of this communication to file ENT of this application. Itted. Note the attached EXA is reason(s) why the oath or the submitted. It be submitted. It is Amendment / Comment or Amendment / Comment or Amendment of The Reader according to 37 CF is it of BIOLOGICAL MATE	n No I in this national stage application a reply complying with the requirement of the complying with the requirement of the complex of the comple	irements TICE OF
Attachm nt(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview St Paper No./ 8), 7. ☑ Examiner's	formal Patent Application (PTO- ummary (PTO-413), Mail Date Amendment/Comment Statement of Reasons for Allow Gene N Auduong Primary Examiner Art Unit: 2818	

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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

IN THE SPAECIFICATION:

- Page 1 of the specification has been amended as in the attached page.

Allowable Subject Matter

- 2. Claims 1-39 are allowed.
- 3. The following is an examiner's statement of reasons for allowance:

The prior art does not teach or fairly discloses a method of making a hybrid magnetoelectronic spin-based memory cell as claimed, comprising the steps of: forming an electron spin-based memory element situated on a silicon based substrate; the electron spin-based memory element including: i) a first ferromagnetic layer with a changeable magnetization state; ii) a second ferromagnetic layer with a non-changeable magnetization state; iii) a base layer which is less than 1 micron in thickness and is situated between the first ferromagnetic layer and the second ferromagnetic layer, the base layer comprising a material having electron levels that are not significantly affected by an electron spin; forming a memory cell selector coupled to the electron spin-based memory element, the memory cell selector including a semiconductor based transistor isolation element also situated on the silicon based substrate.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Gene N Auduong whose telephone number is (571) 272-1773.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

GA May 24, 2004

> Gene N Auduong Primary Examiner Art Unit 2818